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022704

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Leonard Forbes et al.

Title: OPERATING A MEMORY DEVICE

Attorney Docket No.: 303.356US4

Customer No.: 21186

22278 U.S. PTO
10/789203
022704

PATENT APPLICATION TRANSMITTAL

MAIL STOP PATENT APPLICATION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

We are transmitting herewith the following attached items and information (as indicated with an "X"):

- ☒ Return postcard.
- ☒ **CONTINUATION** of prior Patent Application No. (08/902133) (under 37 CFR 1.53(b)) comprising:
 - ☒ Specification (40 pgs, including claims numbered 1 through 59 and a 1 page Abstract).
 - ☒ Formal Drawing(s) (7 sheets).
 - ☒ Copy of signed Combined Declaration and Power of Attorney (6 pgs) from prior application.
 - ☒ Incorporation by Reference: *The entire disclosure of the prior application, from which a copy of the oath or declaration is supplied herewith, is considered as being part of the disclosure of the accompanying application and is hereby incorporated by reference therein.*
 - ☒ Check in the amount of \$1816.00 to pay the filing fee.
- ☒ Prior application is assigned of record to Micron Technology, Inc.
- ☒ Information Disclosure Statement (1 pgs), Form 1449 (11 pgs) References NOT enclosed, cited in prior application.
- ☒ Communication Concerning Related Applications (3 pgs.).

The filing fee has been calculated below as follows:

	No. Filed	No. Extra	Rate	Fee
TOTAL CLAIMS	59-20	39	x 18.00 =	\$702.00
INDEPENDENT CLAIMS	7-3	4	x 86.00 =	\$344.00
[] MULTIPLE DEPENDENT CLAIMS PRESENTED				\$0.00
BASIC FEE				\$770.00
TOTAL				\$1816.00

Please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

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S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: Unknown

Serial No.: Unknown

Group Art Unit: Unknown

Filed: Herewith

Docket: 303.356US4

Title: OPERATING A MEMORY DEVICE

COMMUNICATION CONCERNING RELATED APPLICATION(S)

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
08/903452	July 29, 1997	303.324US1	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/256643	February 23, 1999	303.324US2	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/652420	August 31, 2000	303.324US3	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/691004	October 18, 2000	303.324US4	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
08/903486	July 29, 1997	303.326US1	SILICON CARBIDE GATE TRANSISTOR
09/259870	March 1, 1999	303.326US2	FABRICATION OF SILICON CARBIDE GATE TRANSISTOR
08/902132	July 29,	303.353US1	TRANSISTOR WITH SILICON

5886368	1997		OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
09/138294 6309907	August 21, 1998	303.353US2	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
08/902843	July 29, 1997	303.354US1	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/135413	August 14, 1998	303.354US2	METHOD FOR OPERATING A MEMORY DEVICE HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/134713	August 14, 1998	303.354US3	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
08/902098 6031263	July 29, 1997	303.355US1	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/140978 6307775	August 27, 1998	303.355US2	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/141392 6249020	August 27, 1998	303.355US3	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/883795	June 18, 2001	303.355US4	METHOD OF FORMING A DEVICE WITH A GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
10/047181	October 23, 2001	303.355US5	MEMORY DEVICE WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
08/902133	July 29, 1997	303.356US1	MEMORY DEVICE
10/231687	August 29,	303.356US2	DYNAMIC ELECTRICALLY

	2002		ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE
08/903453	July 29, 1997	303.378US1	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/258467	February 26, 1999	303.378US2	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/650553	August 30, 2000	303.378US3	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
10/461593	June 11, 2003	303.356US3	MEMORY DEVICE

Respectfully submitted,

LEONARD FORBES ET AL.

By Applicants' Representatives,

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